

B.TECH
(SEM I) THEORY EXAMINATION 2022-23
ELECTRONICS ENGINEERING

Time: 3 Hours**Total Marks: 100****Note:** Attempt all Sections. If require any missing data; then choose suitably.**SECTION A****1. Attempt all questions in brief.****2 x 10 = 20**

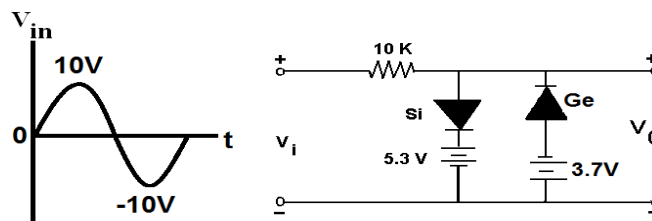
- (a) Describe VI characteristics of the PN junction diode.
- (b) Compare avalanche and zener breakdown mechanisms.
- (c) Describe the benefits of transistor biasing.
- (d) Define the threshold voltage for an E-MOSFET.
- (e) Define the CMRR of an op-amp.
- (f) The output of a particular op-amp increases 8V in 12 μ s. Determine the slew rate.
- (g) Compare analog and digital instruments.
- (h) Write the applications of the digital voltmeter.
- (i) Two sine waves have modulation indexes of 0.4 and 0.3. Determine the modulation index of the combined wave.
- (j) Explain the benefits of modulation.

SECTION B**2. Attempt any three of the following:****10x3=30**

- (a) (i) With the help of a neat diagram, explain the working of the voltage doubler circuit.
 (ii) Write the short note on the tunnel diode.
- (b) Describe the construction and working of an NPN transistor. Define α and β with respect to BJT and derive the relationship between them.
- (c) Explain the concept of virtual ground. Explain the working of op-amp as a differentiator.
- (d) Draw and explain the block diagram of the CRO and also write the applications of CRO.
- (e) Explain modulation for a communication system. Derive the expression for the total power radiated by the modulated signal in amplitude modulation.

SECTION C**3. Attempt any one part of the following:****10x1=10**

- (a) With neat circuit diagram and waveforms explain the working of a bridge full wave rectifier. Explain the advantages of a full-wave rectifier over a half-wave rectifier.
- (b) Determine the output waveform for the given circuit.



4. Attempt any one part of the following:

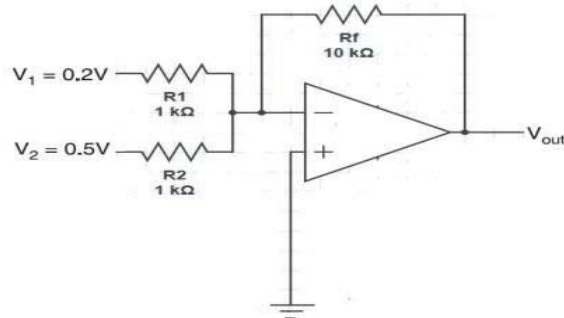
10x1=10

- (a) Draw and explain N-channel depletion type MOSFET with their characteristics curve and also compare enhancement type and depletion type MOSFETs.
- (b) State two differences between BJT and FET. Explain the construction, and working of N-channel JFET with characteristics curve.

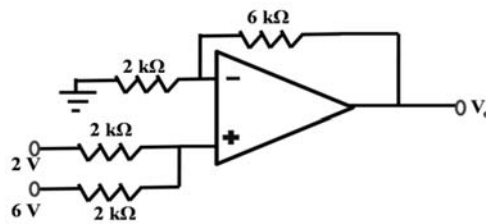
5. Attempt any one part of the following:

10x1=10

- (a) (i) Draw and explain the block diagram of the op-amp. List the ideal characteristics of an op-amp.
(ii) Explain the working of op-amp as an adder.
- (b) Determine the output of the following Circuits(i)



(ii)



6. Attempt any one part of the following:

10x1=10

- (a) Describe the working of a digital multimeter with a proper block diagram and also write its applications.
- (b) Describe the measurement of voltage, frequency & phase using CRO.

7. Attempt any one part of the following:

10x1=10

- (a) Explain amplitude modulation and demodulation with a proper diagram.
- (b) Explain the block diagram of the communication system. A certain transmitter radiates 9 kW with the carrier unmodulated, and 10.125 kW when the carrier is sinusoidally modulated. Calculate the modulation index and percent of modulation.